

Title (en)  
SEMICONDUCTOR LASER

Title (de)  
HALBLEITER-LASER MIT VERTIKALEM RESONATOR

Title (fr)  
LASER A SEMI-CONDUCTEUR

Publication  
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Application  
**EP 02714002 A 20020208**

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Abstract (en)  
[origin: WO02063733A2] In one variation of the invention, a semiconductor laser comprises, in addition to current shields (6), implantation regions in the marginal area of a mesa, said implantation regions acting as mode-selective regions (13). The inner opening of the current shields (6) can thus be larger than that according to prior art. This leads to low ohmic and thermal resistance and enables a high output.

IPC 1-7  
**H01S 5/183**

IPC 8 full level  
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See references of WO 02063733A2

Designated contracting state (EPC)  
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